

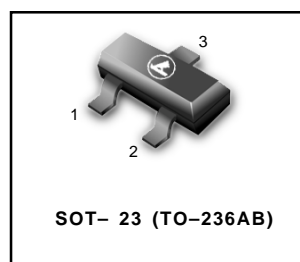
# Digital transistors (built-in resistors)

## LDTD114ELT1

### ●Features

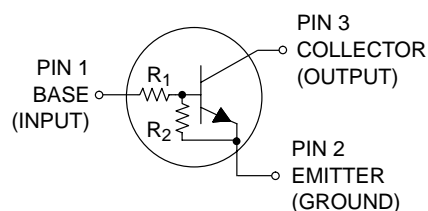
- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thinfilm resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making device design easy.
- 4) Pb-Free package is available.

### LDTD114ELT1



### ●Device marking and ordering information

Device	Marking	Shipping
LDTD114ELT1	CA	3000/Tape&Reel
LDTD114ELT1G(Pb-Free)	CA	3000/Tape&Reel



### ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V <sub>CC</sub>	50	V
Input voltage	V <sub>IN</sub>	-10~+40	V
Output current	I <sub>C</sub>	500	mA
Power dissipation	P <sub>d</sub>	200	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

### ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V <sub>I(off)</sub>	—	—	0.5	V	V <sub>CC</sub> =5V, I <sub>O</sub> =100 μA
	V <sub>I(on)</sub>	3	—	—		V <sub>O</sub> =0.3V, I <sub>O</sub> =10mA
Output voltage	V <sub>O(on)</sub>	—	0.1	0.3	V	I <sub>O</sub> /I <sub>I</sub> =50mA/2.5mA
Input current	I <sub>I</sub>	—	—	0.88	mA	V <sub>I</sub> =5V
Output current	I <sub>O(off)</sub>	—	—	0.5	μA	V <sub>CC</sub> =50V, V <sub>I</sub> =0V
DC current gain	G <sub>I</sub>	56	—	—	—	V <sub>O</sub> =5V, I <sub>O</sub> =50mA
Input resistance	R <sub>I</sub>	7	10	13	kΩ	—
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2	—	—
Transition frequency	f <sub>T</sub>	—	200	—	MHz	V <sub>CE</sub> =10V, I <sub>E</sub> =-50mA, f=100MHz *

\* Transition frequency of the device

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●Electrical characteristic curves

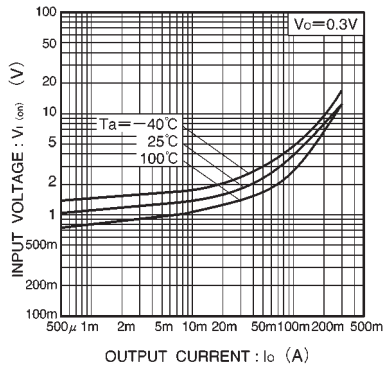


Fig.1 Input voltage vs. output current (ON characteristics)

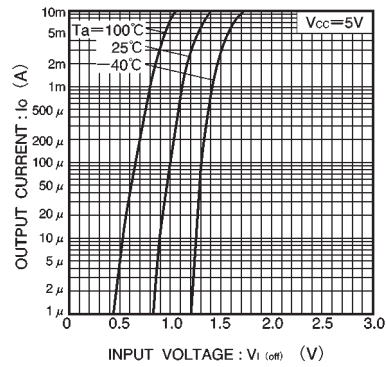


Fig.2 Output current vs. input voltage (OFF characteristics)

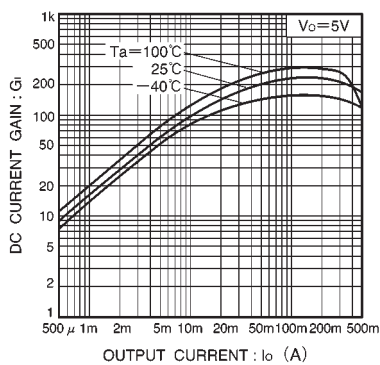


Fig.3 DC current gain vs. output current

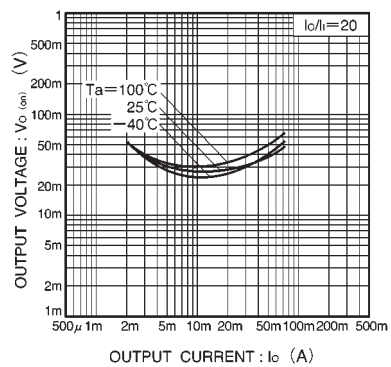
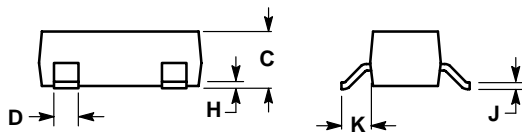
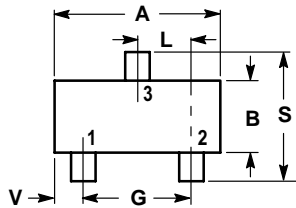


Fig.4 Output voltage vs. output current

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## SOT-23



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

